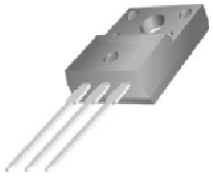
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-220F Plastic-Encapsulate Transistors

2SD2061 TRANSISTOR (NPN)

TO-220F

1. BASE
2. COLLECTOR
3. EMITTER



FEATURES

- Low saturation voltage
- Excellent DC current gain characteristice

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Paramenter	Value	Units
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	3	A
P_C	Collector Power Dissipation	2	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55-150	℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=50μA, I_E=0	80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA, I_B=0	60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=50μA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=60V, I_E=0			10	μA
Emitter cut-off current	I_{EBO}	V_{EB}=4V, I_C=0			10	μA
DC current gain	h_{FE}	V_{CE}=5V, I_C=0.5A	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=2A, I_B=0.2A			1	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=2A, I_B=0.2A			1.5	V
Transition frequency	f_T	V_{CE}=5V, I_C=0.5A, f=5MHz		8		MHz
Collector output capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1MHz		70		pF

Typical Characteristics 2SD2061